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1. (Original) A bipolar transistor comprising:

an emitter comprising an intrinsic emitter portion and an extrinsic emitter portion;

a base comprising an intrinsic base portion in electrical contact with said intrinsic emitter portion and an extrinsic base portion in electrical contact with said intrinsic base portion and electrically isolated from said extrinsic emitter portion by emitter/base spacers, wherein said extrinsic emitter portion is recessed below an upper surface of said extrinsic base portion; and

a collector in electrical contact with said intrinsic base portion.

2. (Original) The bipolar transistor of Claim 1 wherein said extrinsic base portion comprises an upper surface that is silicided to said emitter/base spacers.

3. (Original) The bipolar transistor of Claim 1 wherein said collector further comprises a vertically narrow pedestal dopant region.

4. (Original) The bipolar transistor of Claim 1 wherein each emitter/base spacer of said emitter/base spacers have a width ranging from about 22.5 nm to about 27.5 nm.

6. (Currently Amended) The A bipolar transistor of Claim 5 comprising:

a base comprising an intrinsic base portion in electrical contact with said emitter and an extrinsic base portion in electrical contact with said intrinsic base portion and electrically isolated from said emitter by emitter/base spacers, an upper surface of said extrinsic base portion being silicided to said emitter/base spacers; and

a collector in electrical contact with said intrinsic base portion

wherein said emitter is recessed beneath said upper surface of said extrinsic base portion.

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